

*Concluded  
B1*

an alloy comprising at least one selected from the group consisting of Ge, Sn, Ga, Zn, Pb, In, and Sb existing at least in said contact hole and at a boundary between said conductive layer and said wiring and a vicinity thereof.

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*Sub  
C3  
B2*

5. (Amended) A semiconductor device comprising at least one thin film transistor over a substrate, said thin film transistor comprising:

a conductive layer comprising aluminum;  
an insulating film formed on said conductive layer;  
a contact hole formed through said insulating film;  
a wiring electrically connected with said conductive layer in said contact hole; and

an alloy comprising at least one selected from the group consisting of Ge, Sn, Ga, Zn, Pb, In, and Sb existing at least in said contact hole and at a boundary between said conductive layer and said wiring or a vicinity thereof.

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*Sub  
C4  
B3*

9. (Amended) A semiconductor device comprising at least one thin film transistor over a substrate, said thin film transistor comprising:

two conductive films comprising aluminum electrically connected with each other in a contact hole opened in an insulating film; and

an alloy comprising at least one selected from the group consisting of Ge, Sn, Ga, Zn, Pb, In, and Sb existing at least in said contact hole and at a boundary between said two conductive films and a vicinity thereof.

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Sub  
C5  
12. (Amended) A semiconductor device comprising at least one thin film transistor over a substrate, said thin film transistor comprising:

two conductive films comprising aluminum electrically connected with each other in a contact hole opened in an insulating film; and

an alloy comprising at least one selected from the group consisting of Ge, Sn, Ga, Zn, Pb, In, and Sb existing at least in said contact hole and at a boundary between said two conductive films or a vicinity thereof.

Sub  
C6  
15. (Amended) A semiconductor device comprising at least one thin film transistor over a substrate, said thin film transistor comprising:

a wiring electrode comprising aluminum which is electrically connected to at least a part of said semiconductor device through a contact hole formed through an interlayer insulating film; and

an alloy comprising at least one selected from the group consisting of Ge, Sn, Ga, Zn, Pb, In, and Sb contained in the wiring electrode and existing at least in said contact hole and at a boundary between said wiring electrode and the part of said semiconductor device which one renders the wiring electrode flowable at 450 °C or less.

Sub  
C7  
20. (Amended) A semiconductor device comprising:  
at least one thin film transistor formed over a substrate, said thin film transistor comprising at least a semiconductor region, a gate electrode, and a gate insulating film interposed therebetween;

an interlayer insulating film formed over said thin film transistor;

a contact hole formed through said interlayer insulating film;

a wiring electrically connected with said semiconductor region in said contact hole; and

an alloy comprising at least one selected from the group consisting of Ge, Sn, Ga, Zn, Pb, In, and Sb existing at least in said contact hole and at a boundary between said semiconductor region and said wiring and a vicinity thereof.

24. (Amended) A semiconductor device comprising:  
at least one thin film transistor formed over a substrate, said thin film transistor comprising at least a semiconductor region, a gate electrode, and a gate insulating film interposed therebetween;

an interlayer insulating film formed over said thin film transistor;

a contact hole formed through said interlayer insulating film;

a wiring electrically connected with said semiconductor region in said contact hole; and

an alloy comprising at least one selected from the group consisting of Ge, Sn, Ga, Zn, Pb, In, and Sb existing at least in said contact hole and at a boundary between said semiconductor region and said wiring or a vicinity thereof.